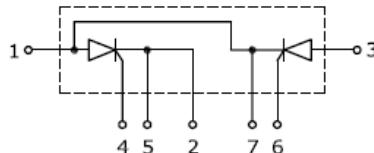


## PRELIMINARY DATASHEET

### Phase Control Thyristor, Half-Bridge Configuration In iQPak™ Power Module Package

- Electrically isolated baseplate
- High surge capability
- General purpose thyristors
- Pb-free lead finish; RoHS compliant



**MAXIMUM RATINGS (per leg)**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Units
Average on-state current $T_C = 79^\circ\text{C}$ , 180°C conduction, half sine wave	$I_{T(\text{AV})}$	35	A
RMS on-state current	$I_{T(\text{RMS})}$	55	
Non-repetitive surge peak on-state current At $t_p=10 \text{ ms}$ , 100% $V_{RRM}$ , sine half-wave, initial $T_j = T_j \text{ max.}$	$I_{TSM}$	500	
Peak gate current	$I_{GM}$	2.5	
Peak reverse and off-state leakage current At $T_j = T_j \text{ max.}$	$I_{RRM} / I_{DRM}$	10	
$I^2t$ value for fusing At $t_p=10 \text{ ms}$ , 100% $V_{RRM}$ , sine half-wave, initial $T_j = T_j \text{ max.}$	$I^2t$	1250	
Repetitive peak off-state voltage	$V_{DRM}$	1200	
Repetitive reverse voltage	$V_{RRM}$	1200	V
Peak gate power At $t_p < 5 \text{ ms}$ , $T_j = T_j \text{ max.}$	$P_{GM}$	10	W
Average gate power At $f=50 \text{ Hz}$ , $T_j = T_j \text{ max.}$	$P_{G(\text{AV})}$	2.5	
Operating junction and storage temperature	$T_j, T_{stg}$	-40... +125	°C

### Thermal and Isolation Characteristics (per leg)

Parameter	Symbol	Max. Value	Units
<b>Characteristics</b>			
Thermal resistance, junction to case	$R_{thJC}$	0.78	K/W
Isolation voltage, RMS (measured between terminals and case)	$V_{iso}$	2500	V

## **Electrical Characteristics (per leg), at $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
I <sub>GT</sub>	Anode supply = 6V, resistive load	-	-	150	mA
V <sub>GT</sub>		-	-	2.5	V
V <sub>GD</sub>	T <sub>j</sub> = 125°C, rated V <sub>DRM</sub>	-	-	0.25	
I <sub>GD</sub>		-	-	6.0	mA
I <sub>H</sub>	T <sub>J</sub> = 25°C	-	-	150	mA
I <sub>L</sub>		-	-	300	
dV/dt	T <sub>j</sub> = T <sub>j</sub> max, linear to 80% V <sub>DRM</sub> , R <sub>g-k</sub> = Open	-	-	1000	V/μs
di/dt	T <sub>J</sub> = T <sub>J</sub> max	-	-	100	A/μs
V <sub>TM</sub>	110A, T <sub>J</sub> = 25°C	-	1.85	-	V
V <sub>T(TO)1</sub>	T <sub>j</sub> = T <sub>j</sub> max	-	1.02	-	
V <sub>T(TO)2</sub>		-	1.23	-	

## Package Outline Drawing

